



# PSMN3R3-80PS

N-channel 80 V, 3.3 mΩ standard level MOSFET in TO-220

Rev. 1 — 27 October 2011

Product data sheet

## 1. Product profile

### 1.1 General description

Standard level N-channel MOSFET in TO-220 package qualified to 175°C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

### 1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive

### 1.3 Applications

- DC-to-DC converters
- Motor control
- Load switch
- Server power supplies

### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{DS}$	drain-source voltage	$T_j \geq 25\text{ °C}$ ; $T_j \leq 175\text{ °C}$	-	-	80	V
$I_D$	drain current	$T_{mb} = 25\text{ °C}$ ; $V_{GS} = 10\text{ V}$ ; see <a href="#">Figure 1</a>	[1]	-	120	A
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ °C}$ ; see <a href="#">Figure 2</a>	-	-	338	W
$T_j$	junction temperature		-55	-	175	°C
<b>Static characteristics</b>						
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}$ ; $I_D = 25\text{ A}$ ; $T_j = 100\text{ °C}$ ; see <a href="#">Figure 12</a>	-	4.6	5.4	mΩ
		$V_{GS} = 10\text{ V}$ ; $I_D = 25\text{ A}$ ; $T_j = 25\text{ °C}$ ; see <a href="#">Figure 13</a>	[2]	2.8	3.3	mΩ
<b>Dynamic characteristics</b>						
$Q_{GD}$	gate-drain charge	$V_{GS} = 10\text{ V}$ ; $I_D = 75\text{ A}$ ; $V_{DS} = 40\text{ V}$ ; see <a href="#">Figure 14</a> ; see <a href="#">Figure 15</a>	-	27	-	nC
$Q_{G(tot)}$	total gate charge		-	139	-	nC
<b>Avalanche ruggedness</b>						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$V_{GS} = 10\text{ V}$ ; $T_{j(init)} = 25\text{ °C}$ ; $I_D = 120\text{ A}$ ; $V_{sup} \leq 80\text{ V}$ ; $R_{GS} = 50\text{ Ω}$ ; unclamped	-	-	676	mJ

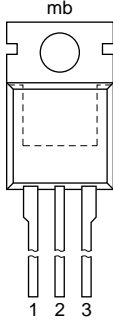
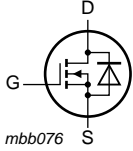
[1] Continuous current is limited by package.

[2] Measured 3 mm from package.



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain		
3	S	source		
mb	D	drain		

SOT78 (TO-220AB)

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN3R3-80PS	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

## 4. Limiting values

**Table 4. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage	$T_j \geq 25\text{ °C}; T_j \leq 175\text{ °C}$	-	80	V
$V_{DGR}$	drain-gate voltage	$T_j \geq 25\text{ °C}; T_j \leq 175\text{ °C}; R_{GS} = 20\text{ k}\Omega$	-	80	V
$V_{GS}$	gate-source voltage		-20	20	V
$I_D$	drain current	$V_{GS} = 10\text{ V}; T_{mb} = 100\text{ °C}$ ; see <a href="#">Figure 1</a> <sup>[1]</sup>	-	120	A
		$V_{GS} = 10\text{ V}; T_{mb} = 25\text{ °C}$ ; see <a href="#">Figure 1</a> <sup>[1]</sup>	-	120	A
$I_{DM}$	peak drain current	pulsed; $t_p \leq 10\text{ }\mu\text{s}$ ; $T_{mb} = 25\text{ °C}$ ; see <a href="#">Figure 3</a>	-	830	A
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ °C}$ ; see <a href="#">Figure 2</a>	-	338	W
$T_{stg}$	storage temperature		-55	175	°C
$T_j$	junction temperature		-55	175	°C
$T_{slid(M)}$	peak soldering temperature		-	260	°C

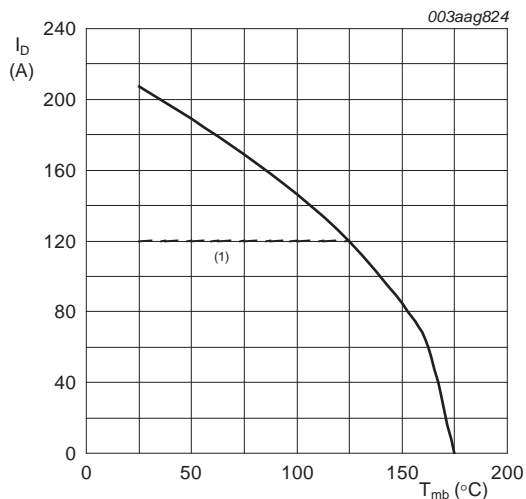
**Source-drain diode**

$I_S$	source current	$T_{mb} = 25\text{ °C}$ <sup>[1]</sup>	-	120	A
$I_{SM}$	peak source current	pulsed; $t_p \leq 10\text{ }\mu\text{s}$ ; $T_{mb} = 25\text{ °C}$	-	830	A

**Avalanche ruggedness**

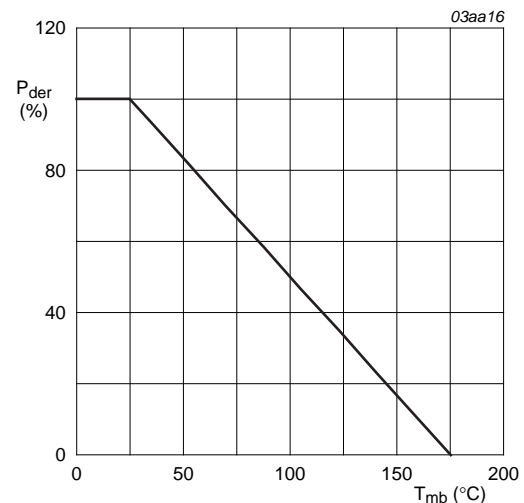
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$V_{GS} = 10\text{ V}; T_{j(\text{init})} = 25\text{ °C}; I_D = 120\text{ A}; V_{sup} \leq 80\text{ V}; R_{GS} = 50\text{ }\Omega$ ; unclamped	-	676	mJ
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[1] Continuous current is limited by package.



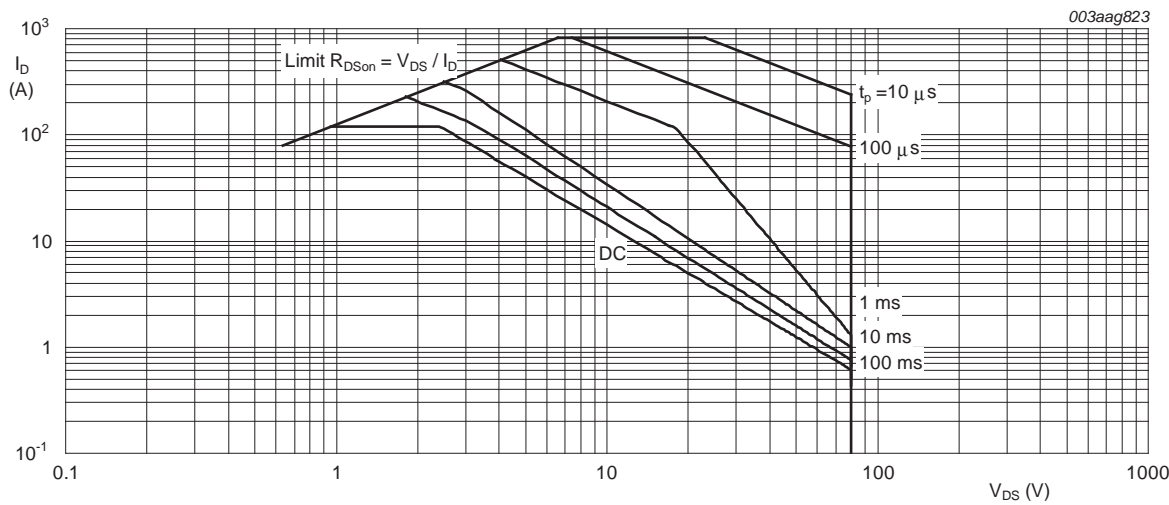
$V_{GS} \geq 10\text{ V}$ ; (1) Capped at 120A due to package

**Fig 1. Continuous drain current as a function of mounting base temperature**



$$P_{der} = \frac{P_{tot}}{P_{tot(25^\circ\text{C})}} \times 100\%$$

**Fig 2. Normalized total power dissipation as a function of mounting base temperature**



$T_{mb} = 25 \text{ }^\circ\text{C}$ ;  $I_{DM}$  is a single pulse; Capped at 120 A due to package

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see <a href="#">Figure 4</a>	-	0.22	0.44	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	Vertical in free air	-	60	-	K/W

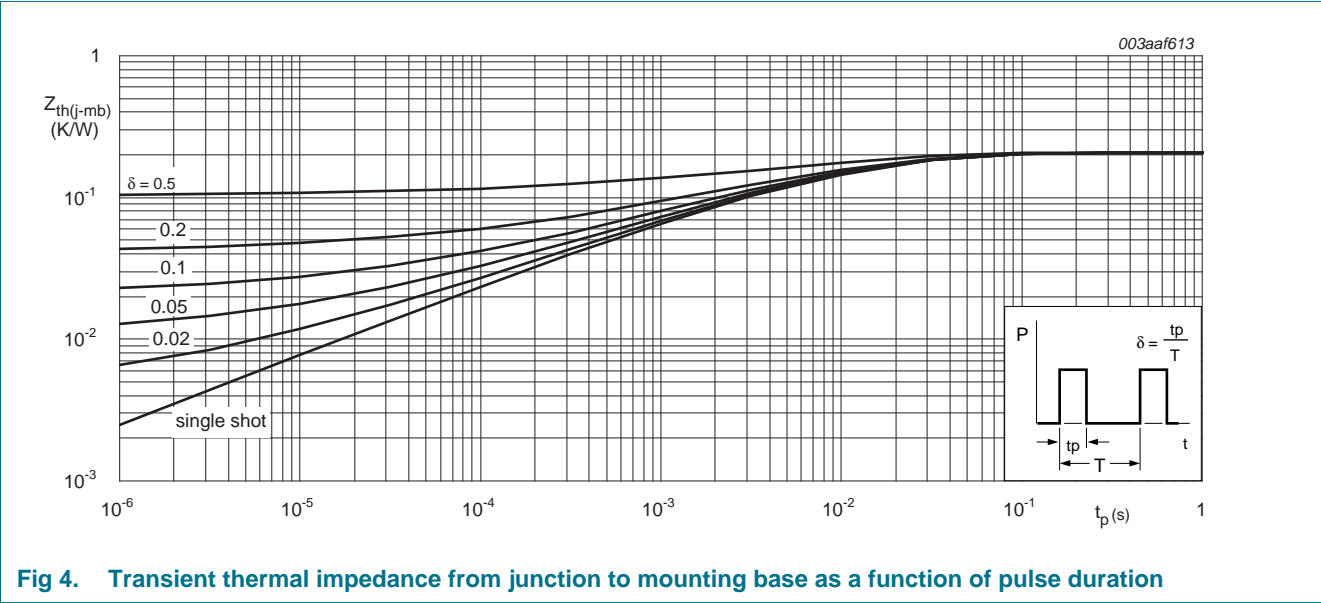


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

## 6. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>J</sub> = -55 °C	73	-	-	V
		I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>J</sub> = 25 °C	80	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>J</sub> = 175 °C; see <a href="#">Figure 10</a>	1	-	-	V
		I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>J</sub> = -55 °C; see <a href="#">Figure 10</a>	-	-	4.6	V
		I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>J</sub> = 25 °C; see <a href="#">Figure 10</a> ; see <a href="#">Figure 11</a>	2	3	4	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 80 V; V <sub>GS</sub> = 0 V; T <sub>J</sub> = 25 °C	-	0.02	10	μA
		V <sub>DS</sub> = 80 V; V <sub>GS</sub> = 0 V; T <sub>J</sub> = 175 °C	-	-	500	μA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>J</sub> = 25 °C	-	-	100	nA
		V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>J</sub> = 25 °C	-	-	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>J</sub> = 175 °C; see <a href="#">Figure 12</a>	-	6.7	7.9	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>J</sub> = 100 °C; see <a href="#">Figure 12</a>	-	4.6	5.4	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>J</sub> = 25 °C; see <a href="#">Figure 13</a>	<a href="#">[1]</a>	-	2.8	3.3
R <sub>G</sub>	internal gate resistance (AC)	f = 1 MHz	-	0.9	-	Ω
Dynamic characteristics						
Q <sub>G(tot)</sub>	total gate charge	I <sub>D</sub> = 0 A; V <sub>DS</sub> = 0 V; V <sub>GS</sub> = 10 V	-	135	-	nC
		I <sub>D</sub> = 75 A; V <sub>DS</sub> = 40 V; V <sub>GS</sub> = 10 V; see <a href="#">Figure 14</a> ; see <a href="#">Figure 15</a>	-	139	-	nC
Q <sub>GS</sub>	gate-source charge		-	51	-	nC
Q <sub>GS(th)</sub>	pre-threshold gate-source charge		-	30	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate-source charge		-	21	-	nC
Q <sub>GD</sub>	gate-drain charge		-	27	-	nC
V <sub>GS(pl)</sub>	gate-source plateau voltage	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 40 V; see <a href="#">Figure 14</a> ; see <a href="#">Figure 15</a>	-	5.8	-	V
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 40 V; V <sub>GS</sub> = 0 V; f = 1 MHz;	-	9961	-	pF
C <sub>oss</sub>	output capacitance	T <sub>J</sub> = 25 °C; see <a href="#">Figure 16</a>	-	847	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	401	-	pF
t <sub>d(on)</sub>	turn-on delay time	V <sub>DS</sub> = 40 V; R <sub>L</sub> = 0.53 Ω;	-	41	-	ns
t <sub>r</sub>	rise time	V <sub>GS</sub> = 10 V; R <sub>G(ext)</sub> = 10 Ω; I <sub>D</sub> = 75 A	-	43	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	109	-	ns
t <sub>f</sub>	fall time		-	44	-	ns

Table 6. Characteristics ...continued

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Source-drain diode						
$V_{SD}$	source-drain voltage	$I_S = 25\text{ A}$ ; $V_{GS} = 0\text{ V}$ ; $T_j = 25\text{ °C}$ ; see Figure 17	-	0.8	1.2	V
$t_{rr}$	reverse recovery time	$I_S = 25\text{ A}$ ; $dI_S/dt = 100\text{ A/}\mu\text{s}$ ;	-	63	-	ns
$Q_r$	recovered charge	$V_{GS} = 0\text{ V}$ ; $V_{DS} = 20\text{ V}$	-	121	-	nC

[1] Measured 3 mm from package.

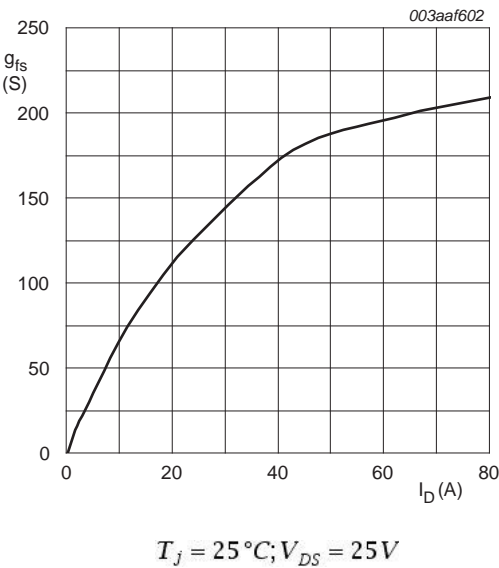


Fig 5. Forward transconductance as a function of drain current; typical values

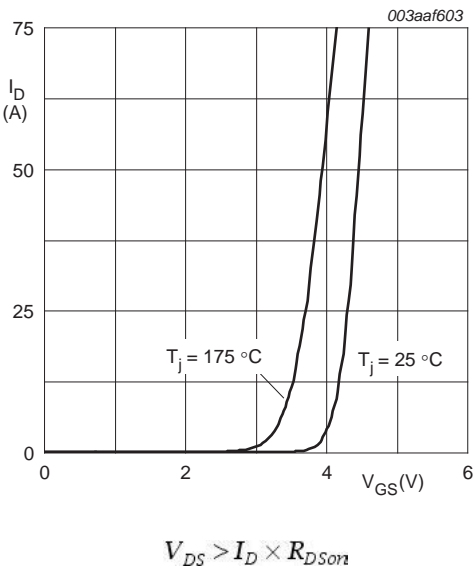


Fig 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values

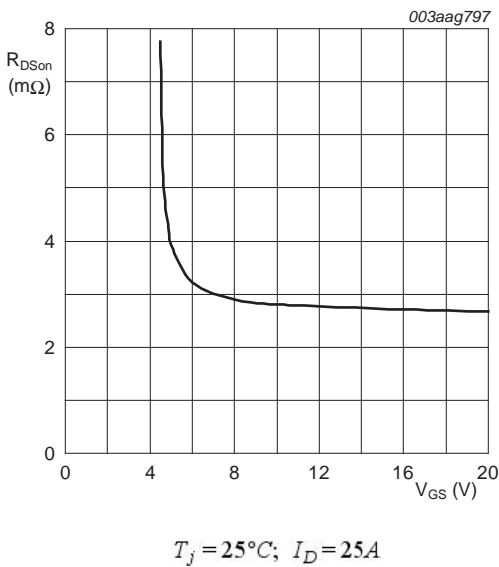


Fig 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

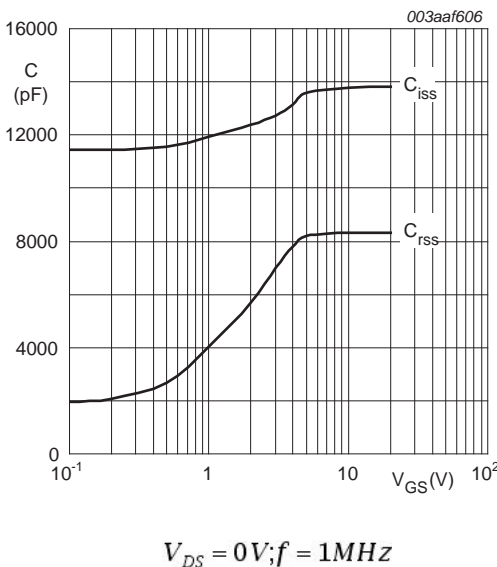


Fig 8. Input and reverse transfer capacitances as a function of gate-source voltage; typical values

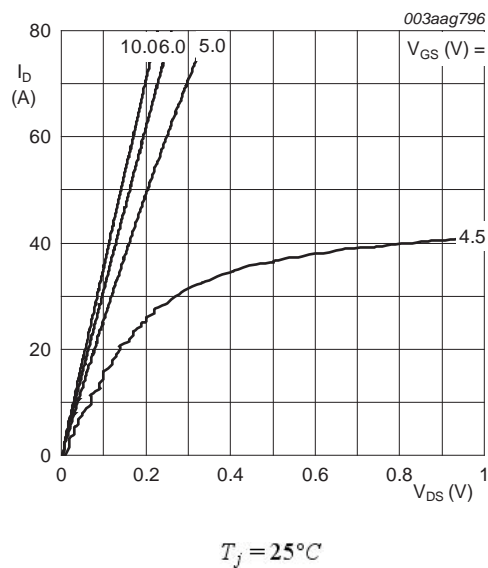


Fig 9. Output characteristics; drain current as a function of drain-source voltage; typical values

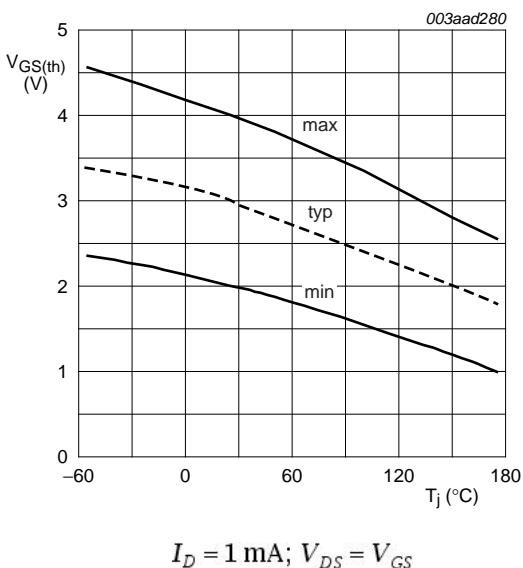


Fig 10. Gate-source threshold voltage as a function of junction temperature

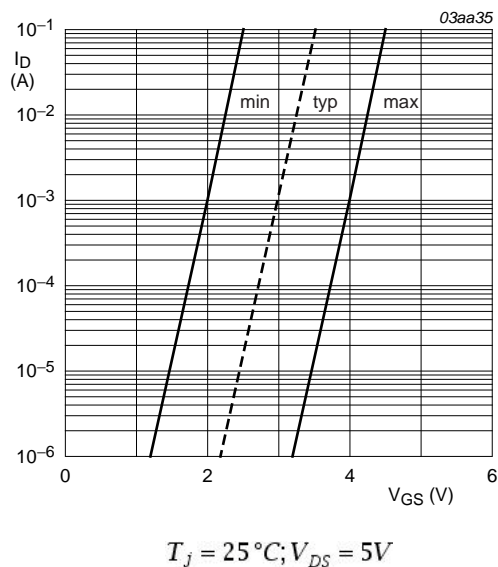


Fig 11. Sub-threshold drain current as a function of gate-source voltage

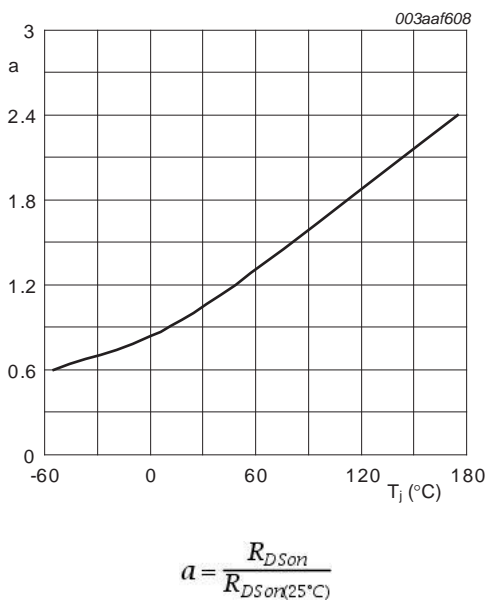


Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature



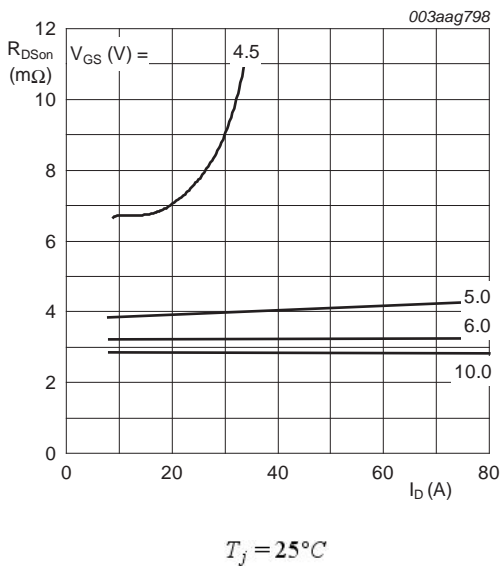


Fig 13. Drain-source on-state resistance as a function of drain current; typical values

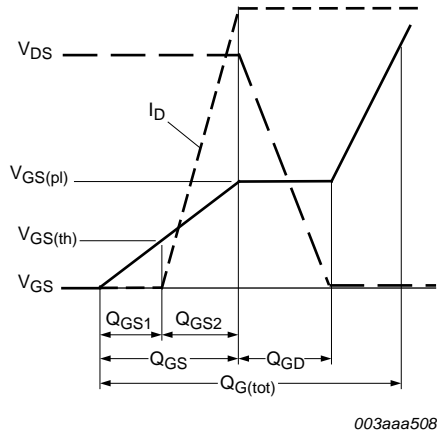


Fig 14. Gate charge waveform definitions

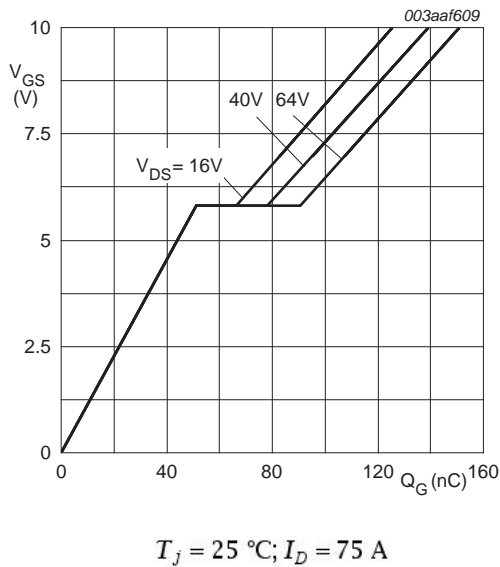


Fig 15. Gate-source voltage as a function of gate charge; typical values

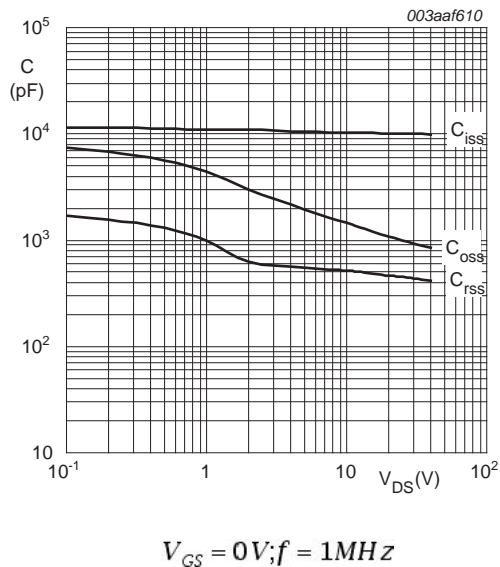


Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

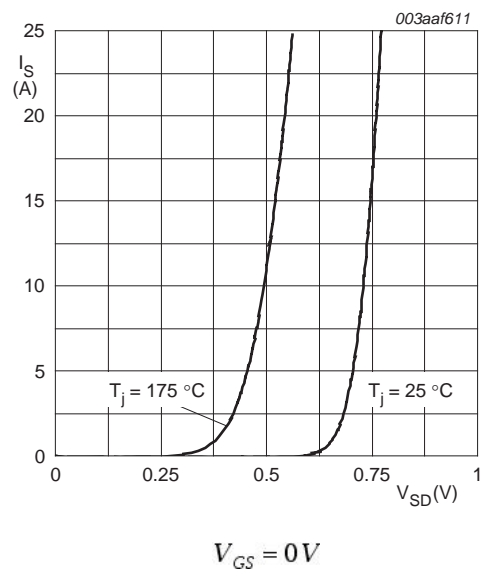


Fig 17. Source current as a function of source-drain voltage; typical values

7. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB SOT78

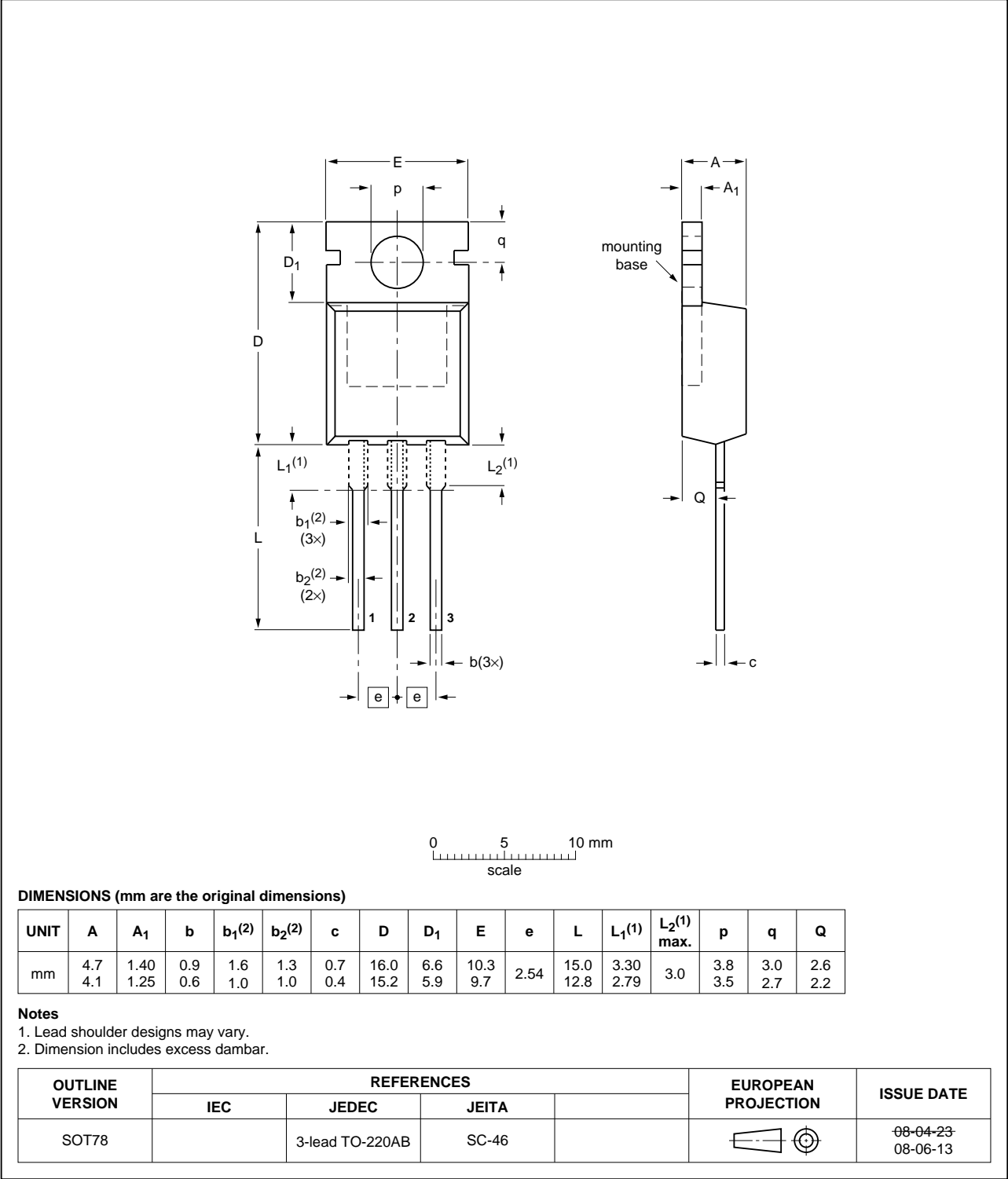


Fig 18. Package outline SOT78 (TO-220AB)

## 8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN3R3-80PS v.1	20111027	Product data sheet	-	-

## 9. Legal information

### 9.1 Data sheet status

Document status <sup>[1] [2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".

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